

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	0.38Ω@4.5V	0.75A
	0.45Ω@2.5V	

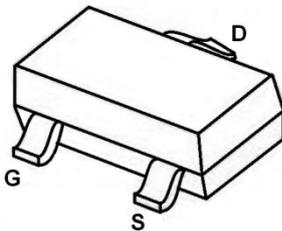
Feature

- High power and current handling capability
- Surface mount package
- ESD protected

Application

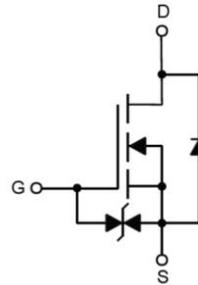
- Battery switch
- DC/DC converter

Package

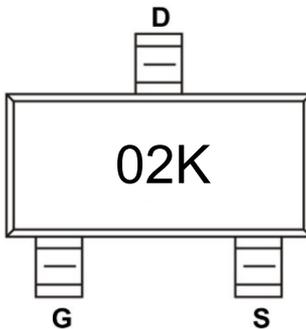


SOT-323

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	0.75	A
Pulsed Drain Current	I_{DM}	3	A
Power Dissipation	P_D	0.2	W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Operating Junction Temperature	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

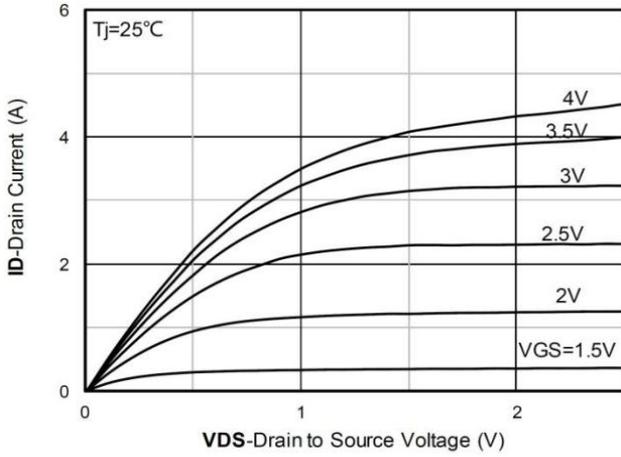
Electrical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero Gate voltage drain current	I_{DSS}	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$			± 10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.3	0.65	1	V
Drain-Source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 0.5\text{A}$		0.25	0.38	Ω
		$V_{GS} = 2.5\text{V}, I_D = 0.2\text{A}$		0.35	0.45	
Dynamic characteristics¹⁾						
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		35		pF
Output capacitance	C_{oss}			19		
Reverse transfer capacitance	C_{rss}			9		
Total Gate Charge	Q_g	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 0.5\text{A}$		0.8		nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.16		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 0.5\text{A}$ $R_G = 10\Omega$		4		nS
Turn-on rise time	t_r			19		
Turn-off delay time	$t_{d(off)}$			10		
Turn-off fall time	t_f			21		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				0.75	A
Diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}, I_S = 1\text{A}, T_J = 25^\circ\text{C}$			1.2	V

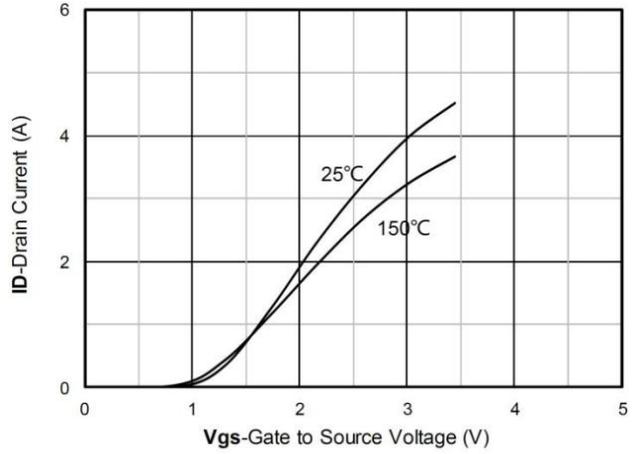
Notes:

1) Guaranteed by design, not subject to production testing.

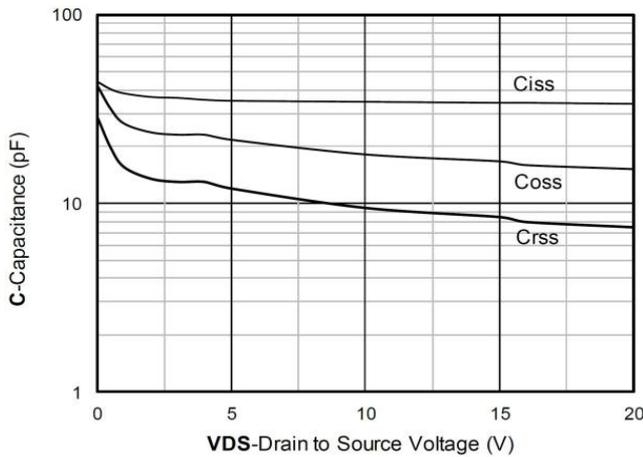
Typical Characteristics



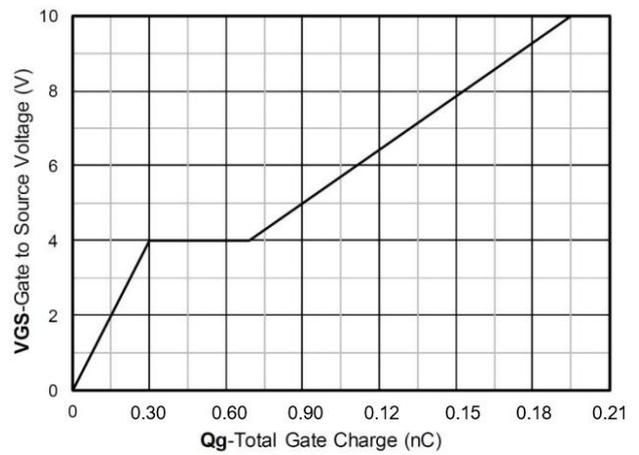
Output Characteristics



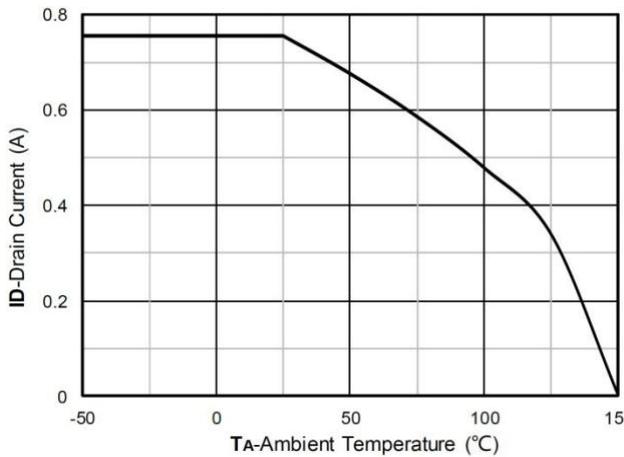
Transfer Characteristics



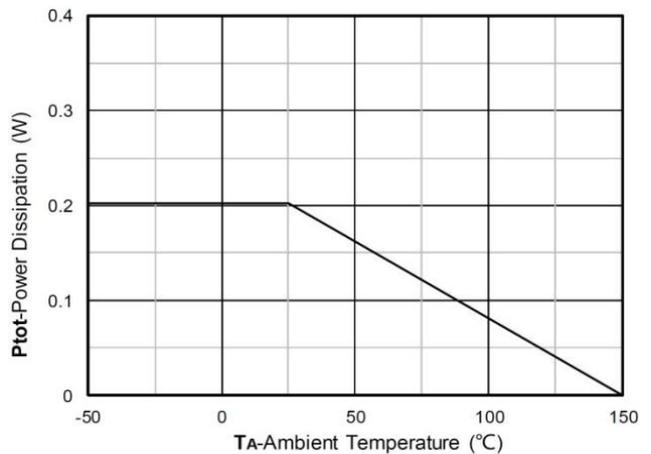
Capacitance Characteristics



Gate Charge

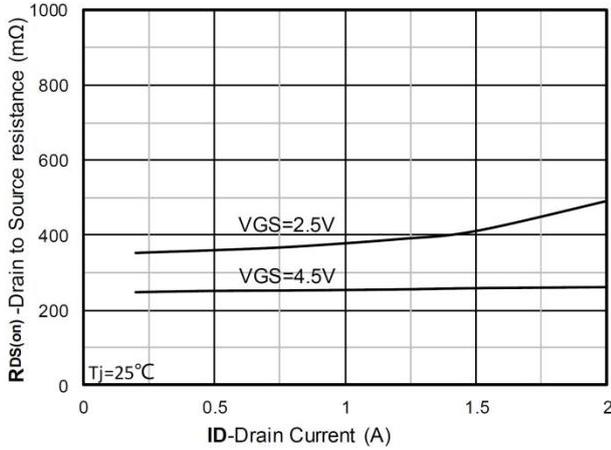


Current dissipation

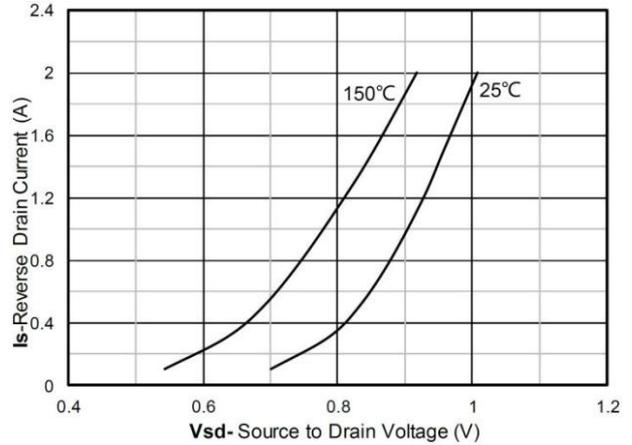


Power dissipation

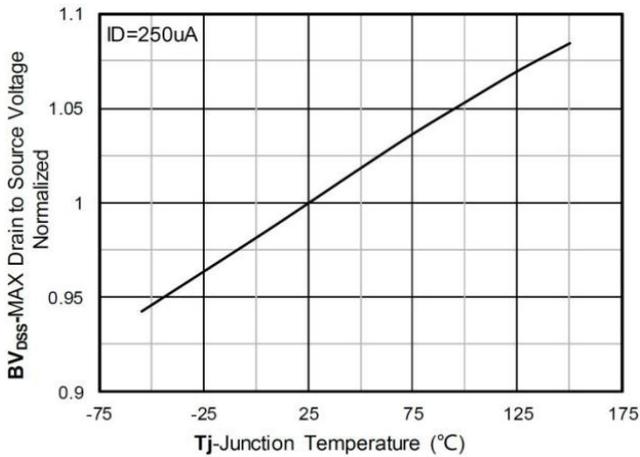
Typical Characteristics



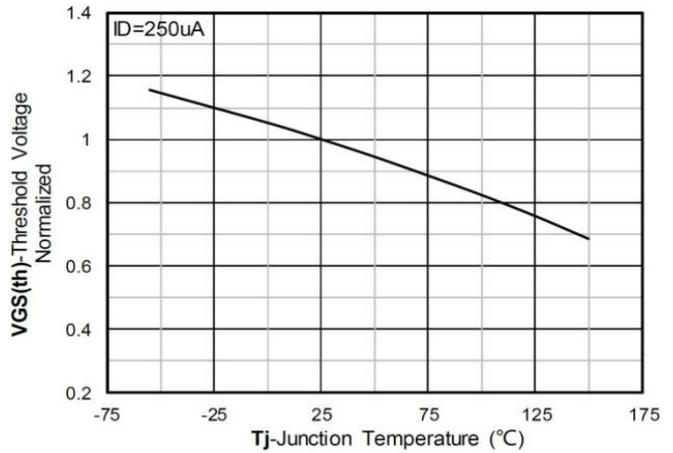
RDS(on) VS Drain Current



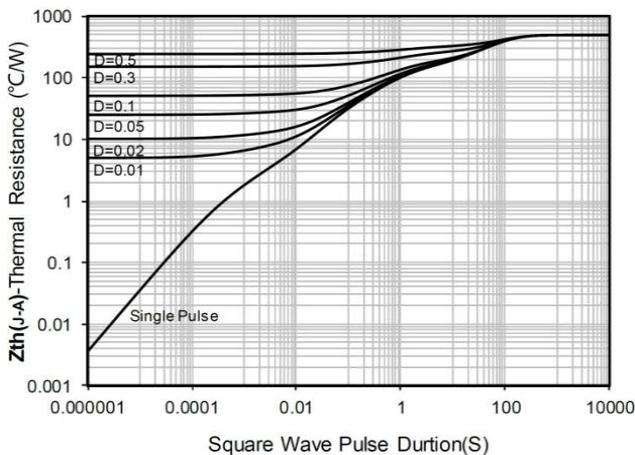
Forward characteristics of reverse diode



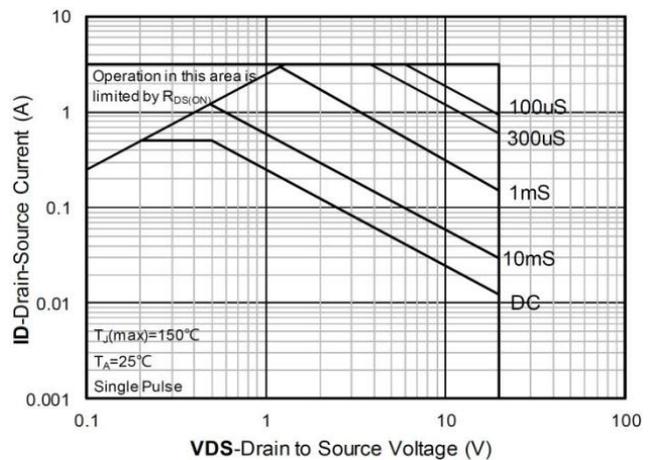
Normalized breakdown voltage



Normalized Threshold voltage

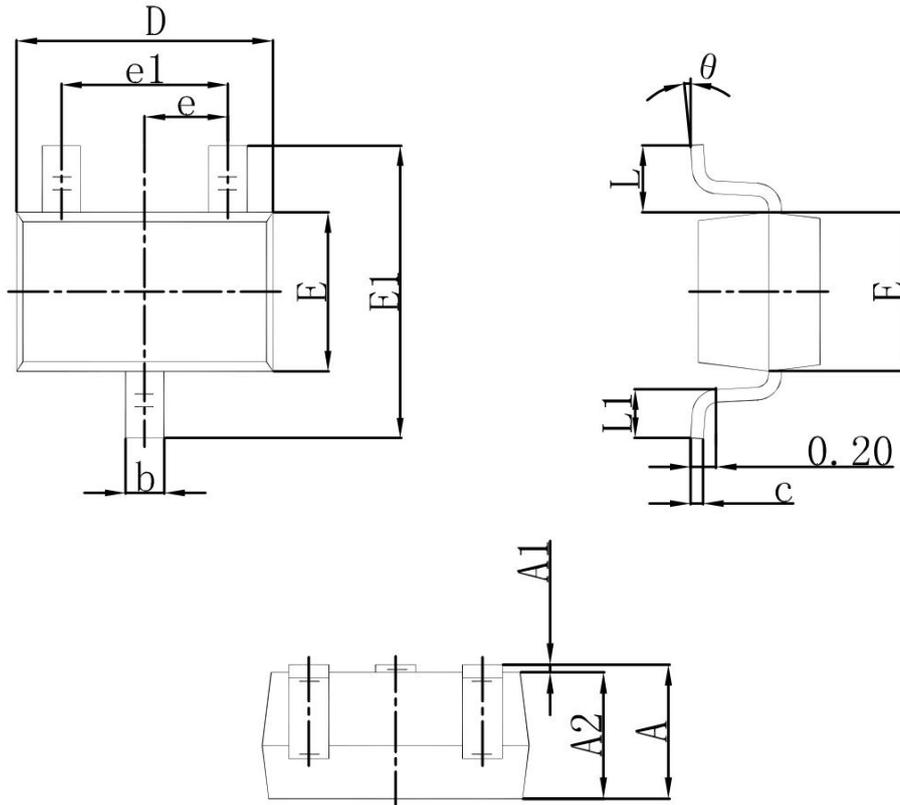


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.000	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.250	0.460	0.010	0.018
θ	0°	8°	0°	8°